a2

[0004] One limitation to achieving smaller sizes of IC device features is the capability of conventional lithography. Lithography is the process by which a pattern or image is transferred from one medium to another. Conventional IC lithography uses ultra-violet (UV) sensitive photoresist. Ultra-violet light is projected to the photoresist through a reticle or mask to create device patterns on an IC. Conventional IC lithographic processes are limited in their ability to print small features, such as contacts, trenches, polysilicon lines or gate structures.

a3

[0032] Reflective metal layer 214 can be tungsten (W) or any other reflective metal. ARC layer 216 can be SiN, SiON, SiRN, or any other suitable material having appropriate anti-reflective properties. ARC layer 216 is located above reflective metal layer 214 and polysilicon layer 212. In an exemplary embodiment, ARC layer 216 has a thickness of 400-800 Angstroms and reflective metal layer 214 has a thickness of 80-200 Angstroms.

In the Claims:

In accordance with 37 C.F.R. § 1.121, please substitute for original Claims 2, 12, 15, 16, and 20 the following rewritten versions of the same claims, as amended. The changes are shown explicitly in the attached "Version with Markings to Show Changes Made".

a4

2. (Once Amended) The method of claim 1, further comprising depositing a resist layer over the anti-reflective coating.

a5

12. (Once Amended) The method of claim 7, wherein the reflective metal layer is optically opaque to the gate material layer.

a6

15. (Once Amended) The method of claim 14, wherein the reflective metal layer comprises tungsten (W).

16. (Once Amended) The method of claim 14, wherein the metal material layer has a thickness of approximately 100 Angstroms.

a7

20. (Once Amended) The method of claim 19, wherein the reflective metal layer has a thickness of between 80 and 200 Angstroms.